EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1978	(semiconductor or semi adj conductor) same ((zirconium or zr or yttrium or yt) adj oxide)	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 08:01
L3	72	(semiconductor or semi adj conductor) same ((zirconium or zr or yttrium or yt) adj oxide) adj layer	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 08:01
L5	2	("6783875").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/08 08:15
L6	3	(semiconductor or semi adj conductor) same ((zirconium or zr or yttrium or yt) adj oxide) adj layer same plasma	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 08:23
L7	140	(semiconductor or semi adj conductor) same ((zirconium or zr or yttrium or yt) adj oxide) same plasma	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 08:24
L8	11780	(semiconductor or semi adj conductor) same (clean$3 or strip$3 or etch$3) same (HF or hydrofluoric or nitric or "HNO.sub.3")	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 10:02
L9	1326	(semiconductor or semi adj conductor) same (clean$3 or strip$3 or etch$3) same ((HF or hydrofluoric) near7 (nitric or "HNO.sub.3"))	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 10:03
L10	7529	427/248.1,255.18,255.19,271,275,290,292,307,452,455,456.ccls. or "438,694,778,785,798,800,692,693,694".ccls. or "216,37,52,53,89,83,96,99,102,108".ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 10:05
L11	3	l9 and l10	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 10:05
L12	1	(semiconductor or semi adj conductor) same (clean$3 or strip$3 or etch$3) same plasma same (compress$3 adj air)	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 11:17
L13	11	(semiconductor or semi adj conductor) same plasma same (compress$3 adj air)	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 11:18
L14	108	(semiconductor or semi adj conductor) same plasma adj form$3 adj gas	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 11:33
L15	1460	(semiconductor or semi adj conductor) same (clean$3 or strip$3 or etch$3) same roughness	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 12:22

L16	3	L15 and L10	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 12:22
L17	61	(semiconductor or semi adj conductor) same (clean$3 or strip$3 or etch$3) same roughness same Ra	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 12:24
L18	42	(semiconductor or semi adj conductor) same (strip$3 or etch$3) same roughness same Ra	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 12:36
L19	59	(semiconductor or semi adj conductor) same (strip$3 or etch$3 or grind$3) same roughness same Ra	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 12:39
L20	13	(semiconductor or semi adj conductor) same (strip$3 or etch$3 or grind$3) same rough$3 same Ra	US-PGPUB; USPAT; USOCR	OR	ON	2008/02/08 12:39
S1	0	("Davis-ianorlaube-david.in.").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/07 14:37
S2	14	Davis-ian or laube-david.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/07 14:38
S3	21408	(boc adj (edwards or group) or Applied adj materials).as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/07 14:47
S4	7533	rough$5 and acid and metal adj oxide and plasma	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/07 14:48

S5	47	S3 and S4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/07 14:50
S6	36	("20020086118" | "20020094686" | "200301118731" | "20030221702" | "4842897" | "5202008" | "5391275" | "5651797" | "5916454" | "6063142" | "6221269" | "6296716" | "6479108" | "6504233" | "6565667" | "6613603" | "6632689" | "6663914").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/07 14:57
S7	2	EP-1158072-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/07 14:57
S8	2	("6656535").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/07 15:57

2/8/2008 1:28:27 PM

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